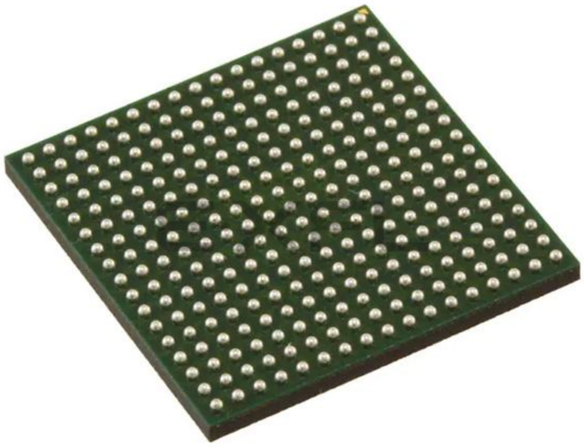
Microchip Technology - AGLP125V5-CSG289I Datasheet



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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	3120
Total RAM Bits	36864
Number of I/O	212
Number of Gates	125000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	289-TFBGA, CSBGA
Supplier Device Package	289-CSP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/aglp125v5-csg289i

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

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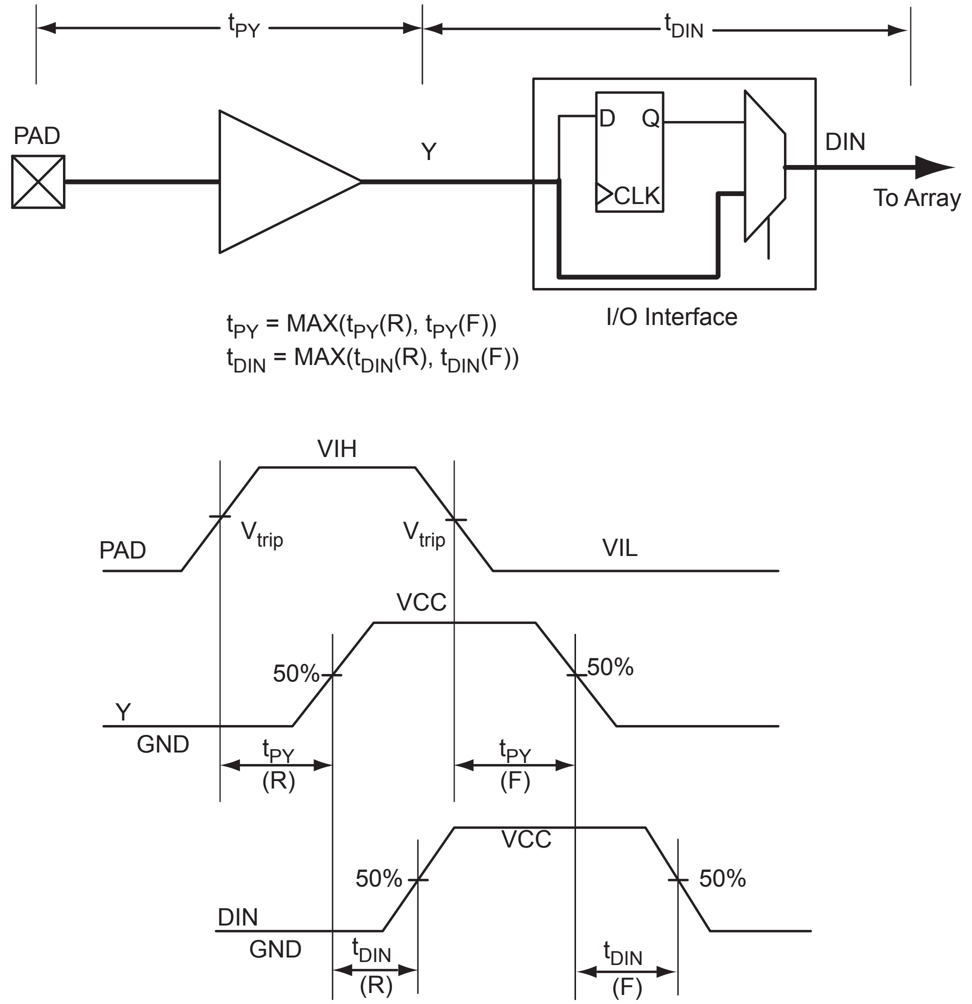


Figure 2-4 • **Input Buffer Timing Model and Delays (example)**

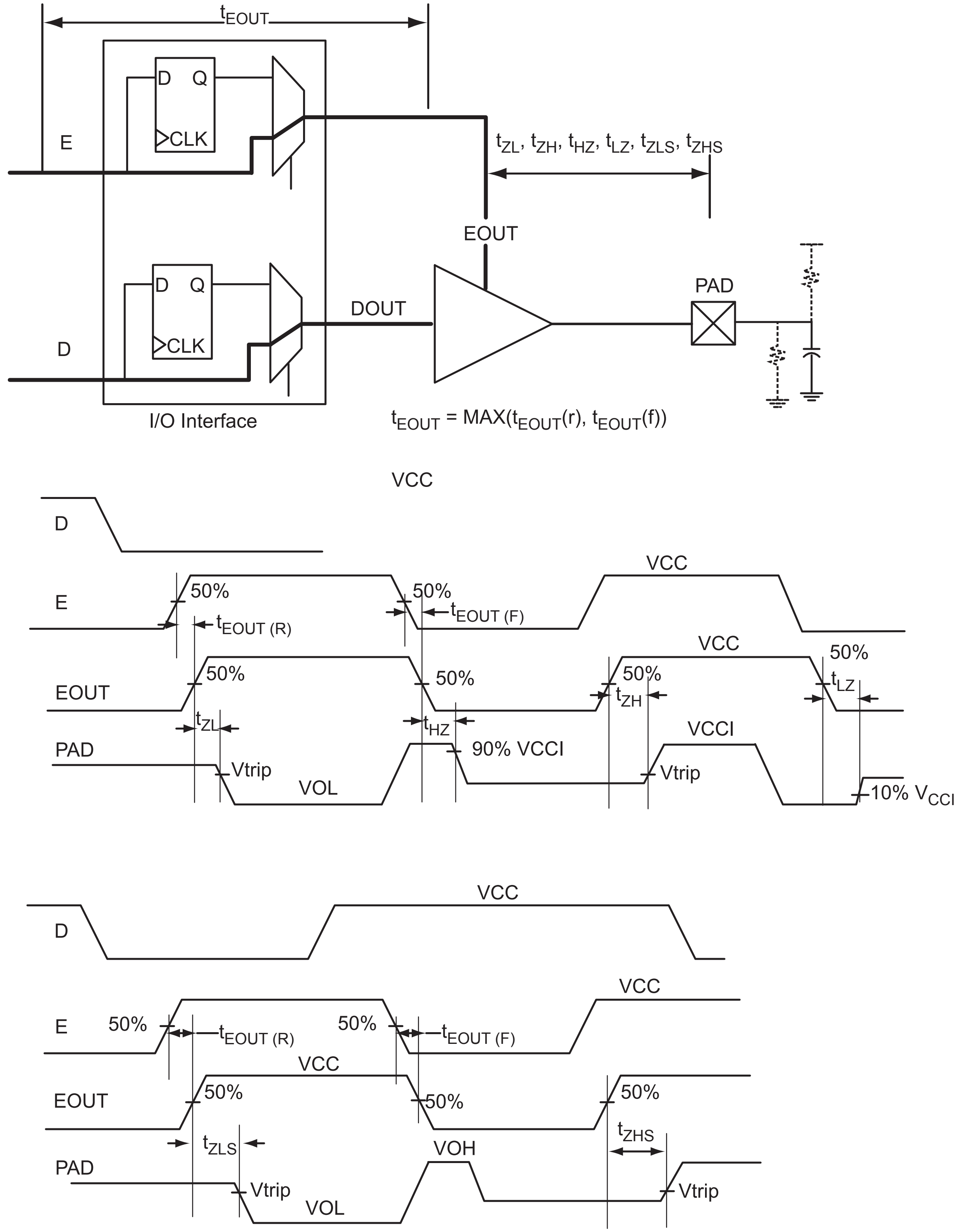


Figure 2-6 • **Tristate Output Buffer Timing Model and Delays (example)**

Detailed I/O DC Characteristics

Table 2-27 **• Input Capacitance**

Symbol	Definition	Conditions	Min.	Max.	Units
C_{IN}	Input capacitance	VIN = 0, f = 1.0 MHz		8	pF
C_{INCLK}	Input capacitance on the clock pin	VIN = 0, f = 1.0 MHz		8	pF

Table 2-28 **• I/O Output Buffer Maximum Resistances** [1]

Standard	Drive Strength	$R_{PULL\text{-}DOWN}$ (Ω) [2]	$R_{PULL\text{-}UP}$ (Ω) [3]
3.3 V LVTTL / 3.3V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range	100 µA	Same as equivalent software default drive	
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
1.2 V LVCMOS	2 mA	157.5	163.8
1.2 V LVCMOS Wide Range[4]	100 µA	157.5	163.8

Notes:

1. *These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCC_I, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS model on the Microsemi SoC Products Group website at http://www.microsemi.com/soc/download/ibis/default.aspx.*
2. $R_{(PULL\text{-}DOWN\text{-}MAX)}$ = *(VOLspec) / IOLspec*
3. $R_{(PULL\text{-}UP\text{-}MAX)}$ = *(VCCImax – VOHspec) / IOHspec*
4. *Applicable to IGLOO PLUS V2 devices operating at VCCI ≥ VCC.*

The length of time an I/O can withstand IOSH/IOSL events depends on the junction temperature. The reliability data below is based on a 3.3 V, 12 mA I/O setting, which is the worst case for this type of analysis.

For example, at 100°C, the short current condition would have to be sustained for more than six months to cause a reliability concern. The I/O design does not contain any short circuit protection, but such protection would only be needed in extremely prolonged stress conditions.

***Table 2-31* • Duration of Short Circuit Event before Failure**

Temperature	Time before Failure
–40°C	> 20 years
0°C	> 20 years
25°C	> 20 years
70°C	5 years
85°C	2 years
100°C	6 months

***Table 2-32* • Schmitt Trigger Input Hysteresis**
Hysteresis Voltage Value (Typ.) for Schmitt Mode Input Buffers

Input Buffer Configuration	Hysteresis Value (typ.)
3.3 V LVTTL/LVCMOS (Schmitt trigger mode)	240 mV
2.5 V LVCMOS (Schmitt trigger mode)	140 mV
1.8 V LVCMOS (Schmitt trigger mode)	80 mV
1.5 V LVCMOS (Schmitt trigger mode)	60 mV
1.2 V LVCMOS (Schmitt trigger mode)	40 mV

***Table 2-33* • I/O Input Rise Time, Fall Time, and Related I/O Reliability**

Input Buffer	Input Rise/Fall Time (min.)	Input Rise/Fall Time (max.)	Reliability
LVTTL/LVCMOS (Schmitt trigger disabled)	No requirement	10 ns *	20 years (100°C)
LVTTL/LVCMOS (Schmitt trigger enabled)	No requirement	No requirement, but input noise voltage cannot exceed Schmitt hysteresis.	20 years (100°C)

Note: **The maximum input rise/fall time is related to the noise induced into the input buffer trace. If the noise is low, then the rise time and fall time of input buffers can be increased beyond the maximum value. The longer the rise/fall times, the more susceptible the input signal is to the board noise. Microsemi recommends signal integrity evaluation/characterization of the system to ensure that there is no excessive noise coupling into input signals.*

Applies to 1.2 V DC Core Voltage

Table 2-44 • **3.3 V LVCMOS Wide Range Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	4 mA	STD	0.98	6.68	0.19	1.32	1.92	0.67	6.68	5.74	3.13	3.47	ns
100 µA	6 mA	STD	0.98	5.51	0.19	1.32	1.92	0.67	5.51	4.94	3.48	4.11	ns
100 µA	8 mA	STD	0.98	5.51	0.19	1.32	1.92	0.67	5.51	4.94	3.48	4.11	ns
100 µA	12 mA	STD	0.98	4.75	0.19	1.32	1.92	0.67	4.75	4.36	3.73	4.52	ns
100 µA	16 mA	STD	0.98	4.75	0.19	1.32	1.92	0.67	4.75	4.36	3.73	4.52	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Table 2-45 • **3.3 V LVCMOS Wide Range High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
100 µA	4 mA	STD	0.98	4.16	0.19	1.32	1.92	0.67	4.16	3.32	3.12	3.66	ns
100 µA	6 mA	STD	0.98	3.54	0.19	1.32	1.92	0.67	3.54	2.79	3.48	4.31	ns
100 µA	8 mA	STD	0.98	3.54	0.19	1.32	1.92	0.67	3.54	2.79	3.48	4.31	ns
100 µA	12 mA	STD	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns
100 µA	16 mA	STD	0.98	3.21	0.19	1.32	1.92	0.67	3.21	2.52	3.73	4.73	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
3. *Software default selection highlighted in gray.*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-54 • **1.8 V LVCMOS Low Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	5.89	0.18	1.00	1.43	0.66	6.01	5.43	1.78	1.30	ns
4 mA	STD	0.97	4.82	0.18	1.00	1.43	0.66	4.92	4.56	2.08	2.08	ns
6 mA	STD	0.97	4.13	0.18	1.00	1.43	0.66	4.21	3.96	2.30	2.46	ns
8 mA	STD	0.97	4.13	0.18	1.00	1.43	0.66	4.21	3.96	2.30	2.46	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-55 • **1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.97	2.82	0.18	1.00	1.43	0.66	2.88	2.78	1.78	1.35	ns
4 mA	STD	0.97	2.30	0.18	1.00	1.43	0.66	2.35	2.11	2.08	2.15	ns
6 mA	STD	0.97	2.00	0.18	1.00	1.43	0.66	2.04	1.76	2.29	2.55	ns
8 mA	STD	0.97	2.00	0.18	1.00	1.43	0.66	2.04	1.76	2.29	2.55	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Applies to 1.2 V DC Core Voltage

Table 2-56 • **1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	6.43	0.19	1.12	1.61	0.67	6.54	5.93	2.19	1.88	ns
4 mA	STD	0.98	5.33	0.19	1.12	1.61	0.67	5.41	5.03	2.50	2.68	ns
6 mA	STD	0.98	4.61	0.19	1.12	1.61	0.67	4.69	4.41	2.72	3.07	ns
8 mA	STD	0.98	4.61	0.19	1.12	1.61	0.67	4.69	4.41	2.72	3.07	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-57 • **1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	3.30	0.19	1.12	1.61	0.67	3.34	3.21	2.19	1.93	ns
4 mA	STD	0.98	2.76	0.19	1.12	1.61	0.67	2.79	2.51	2.50	2.76	ns
6 mA	STD	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns
8 mA	STD	0.98	2.45	0.19	1.12	1.61	0.67	2.48	2.16	2.71	3.16	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

1.2 V LVCMOS (JESD8-12A)

Low-Voltage CMOS for 1.2 V complies with the LVCMOS standard JESD8-12A for general purpose 1.2 V applications. It uses a 1.2 V input buffer and a push-pull output buffer.

***Table 2-64* • Minimum and Maximum DC Input and Output Levels**

1.2 V LVCMOS[1]	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL[2]	IIH[3]
Drive Strength	**Min. V**	**Max. V**	**Min. V**	**Max. V**	**Max. V**	**Min. V**	**mA**	**mA**	**Max. mA[4]**	**Max. mA[4]**	**μA[5]**	**μA[5]**
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	20	26	10	10

Notes:

1. *Applicable to IGLOO nano V2 devices operating at VCCI ≥ VCC.*
2. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
3. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges.*
4. *Currents are measured at high temperature (100°C junction temperature) and maximum voltage.*
5. *Currents are measured at 85°C junction temperature.*
6. *Software default selection highlighted in gray.*

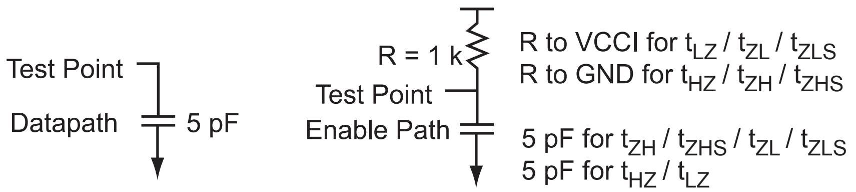


***Figure 2-11* • AC Loading**

***Table 2-65* • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)	C_{LOAD} (pF)
0	1.2	0.6	5

Note: *Measuring point = Vtrip. See Table 2-23 on page 2-20 for a complete table of trip points.*

Timing Characteristics

Applies to 1.2 V DC Core Voltage

***Table 2-66* • 1.2 V LVCMOS Low Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	8.27	0.19	1.57	2.34	0.67	7.94	6.77	3.00	3.11	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

***Table 2-67* • 1.2 V LVCMOS High Slew**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.14 V

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{PYS}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	STD	0.98	3.38	0.19	1.57	2.34	0.67	3.26	2.78	2.99	3.24	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*
2. *Software default selection highlighted in gray.*

Table 2-72 • **Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	H, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	F, H
t_{OHD}	Data Hold Time for the Output Data Register	F, H
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	L, DOUT
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	L, H
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	L, H
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	H, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	J, H
t_{OEHD}	Data Hold Time for the Output Enable Register	J, H
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	I, EOUT
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	I, H
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	I, H
t_{ICLKQ}	Clock-to-Q of the Input Data Register	A, E
t_{ISUD}	Data Setup Time for the Input Data Register	C, A
t_{IHD}	Data Hold Time for the Input Data Register	C, A
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	D, E
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	D, A
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	D, A

Note: *See Figure 2-12 on page 2-41 for more information.

1.2 V DC Core Voltage

***Table 2-77* • Output Data Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{OCLKQ}	Clock-to-Q of the Output Data Register	1.03	ns
t_{OSUD}	Data Setup Time for the Output Data Register	0.52	ns
t_{OHD}	Data Hold Time for the Output Data Register	0.00	ns
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	1.22	ns
t_{OPRE2Q}	Asynchronous Preset-to-Q of the Output Data Register	1.31	ns
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	0.00	ns
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	0.24	ns
$t_{OREMPRE}$	Asynchronous Preset Removal Time for the Output Data Register	0.00	ns
$t_{ORECPRE}$	Asynchronous Preset Recovery Time for the Output Data Register	0.24	ns
t_{OWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Data Register	0.19	ns
t_{OWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Data Register	0.19	ns
$t_{OCKMPWH}$	Clock Minimum Pulse Width High for the Output Data Register	0.31	ns
$t_{OCKMPWL}$	Clock Minimum Pulse Width Low for the Output Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

1.2 V DC Core Voltage

***Table 2-79* • Output Enable Register Propagation Delays**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	1.06	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.52	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	1.25	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	1.36	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	ns
$t_{OERECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.24	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.24	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.19	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.19	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.31	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-6 for derating values.

1.2 V DC Core Voltage

Table 2-94 • **RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.28	ns
t_{AH}	Address hold time	0.25	ns
t_{ENS}	REN, WEN setup time	1.25	ns
t_{ENH}	REN, WEN hold time	0.25	ns
t_{BKS}	BLK setup time	2.54	ns
t_{BKH}	BLK hold time	0.25	ns
t_{DS}	Input data (DIN) setup time	1.10	ns
t_{DH}	Input data (DIN) hold time	0.55	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	5.51	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	4.77	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	2.82	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – applicable to closing edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – applicable to opening edge	0.32	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – applicable to opening edge	0.44	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.21	ns
	RESET Low to data out Low on DOUT (pipelined)	3.21	ns
$t_{REMRSTB}$	RESET removal	0.93	ns
$t_{RECRSTB}$	RESET recovery	4.94	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.*

Timing Characteristics

1.5 V DC Core Voltage

***Table 2-96* • FIFO**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	1.66	ns
t_{ENH}	REN, WEN Hold Time	0.13	ns
t_{BKS}	BLK Setup Time	0.30	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.63	ns
t_{DH}	Input Data (WD) Hold Time	0.20	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.77	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	1.50	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	2.94	ns
t_{WCKFF}	WCLK High to Full Flag Valid	2.79	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	10.71	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	2.90	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	10.60	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	1.68	ns
	RESET Low to Data Out Low on RD (pipelined)	1.68	ns
$t_{REMRSTB}$	RESET Removal	0.51	ns
$t_{RECRSTB}$	RESET Recovery	2.68	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	0.68	ns
t_{CYC}	Clock Cycle Time	6.24	ns
F_{MAX}	Maximum Frequency for FIFO	160	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.

Embedded FlashROM Characteristics

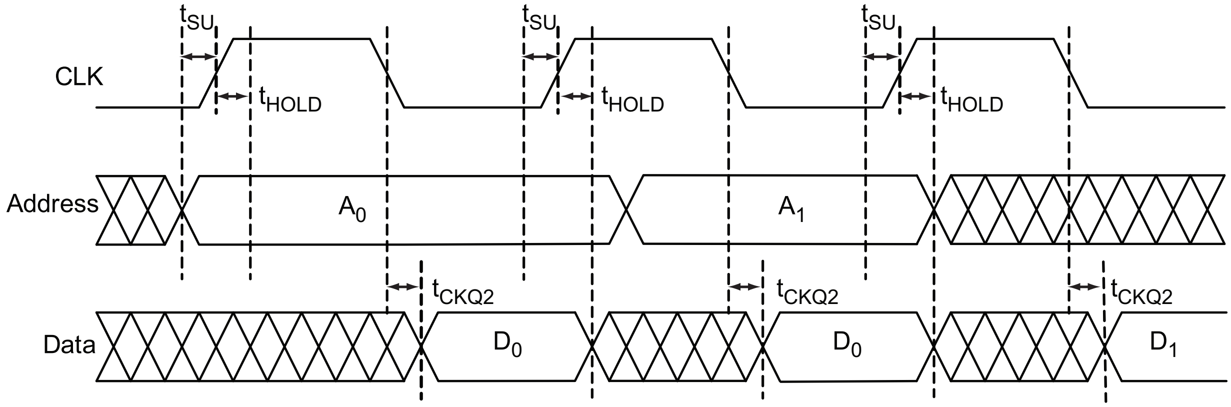


Figure 2-37 • **Timing Diagram**

Timing Characteristics

1.5 V DC Core Voltage

Table 2-98 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.57	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	17.58	ns
F_{MAX}	Maximum Clock Frequency	15	MHz

1.2 V DC Core Voltage

Table 2-99 • **Embedded FlashROM Access Time**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{SU}	Address Setup Time	0.59	ns
t_{HOLD}	Address Hold Time	0.00	ns
t_{CK2Q}	Clock to Out	30.94	ns
F_{MAX}	Maximum Clock Frequency	10	MHz

FF Flash*Freeze Mode Activation Pin

The FF pin is a dedicated input pin used to enter and exit Flash*Freeze mode. The FF pin is active low, has the same characteristics as a single-ended I/O, and must meet the maximum rise and fall times. When Flash*Freeze mode is not used in the design, the FF pin is available as a regular I/O.

When Flash*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash*Freeze mode. While in Flash*Freeze mode, the Flash*Freeze pin should be constantly asserted.

The Flash*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash*Freeze mode and normal operation mode. No user intervention is required.

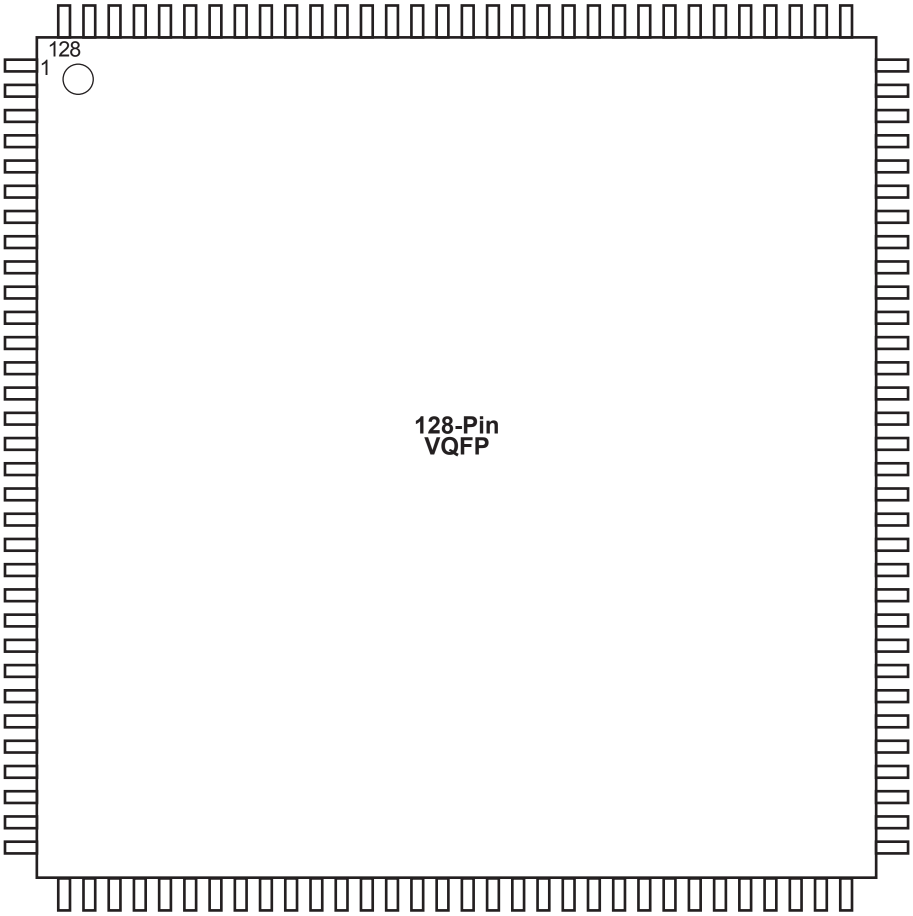
Table 3-1 shows the Flash*Freeze pin location on the available packages for IGLOO and ProASIC3L devices. The Flash*Freeze pin location is independent of device (except for a PQ208 package), allowing migration to larger or smaller IGLOO devices while maintaining the same pin location on the board. Refer to the "Flash*Freeze Technology and Low Power Modes" chapter of the *IGLOO PLUS Device Family User's Guide* for more information on I/O states during Flash*Freeze mode.

***Table 3-1* • Flash*Freeze Pin Location in IGLOO PLUS Devices**

Package	Flash*Freeze Pin
CS281	W2
CS201	R4
CS289	U1
VQ128	34
VQ176	47

4 – Package Pin Assignments

VQ128



Note: This is the top view of the package.

Note

For Package Manufacturing and Environmental information, visit the Resource Center at http://www.microsemi.com/soc/products/solutions/package/docs.aspx.

Pin information is in the "Pin Descriptions" chapter of the *IGLOO PLUS FPGA Fabric User's Guide*.

CS289	
Pin Number	**AGLP125 Function**
G13	IO64RSB1
G14	IO69RSB1
G15	IO78RSB1
G16	IO76RSB1
G17	GND
H1	VCOMPLF
H2	GFB0/IO191RSB3
H3	IO195RSB3
H4	IO197RSB3
H5	IO199RSB3
H6	GFB1/IO192RSB3
H7	GND
H8	GND
H9	GND
H10	GND
H11	GND
H12	GCC1/IO79RSB1
H13	IO74RSB1
H14	GCA0/IO84RSB1
H15	VCCIB1
H16	GCA2/IO85RSB1
H17	GCC0/IO80RSB1
J1	VCCPLF
J2	GFA1/IO190RSB3
J3	VCCIB3
J4	IO185RSB3
J5	IO183RSB3
J6	IO181RSB3
J7	VCC
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO86RSB1
J13	GCB1/IO81RSB1
J14	IO90RSB1
J15	IO89RSB1
J16	GCB0/IO82RSB1
J17	GCA1/IO83RSB1
K1	GND
K2	GFA0/IO189RSB3
K3	GFB2/IO187RSB3
K4	IO179RSB3
K5	IO175RSB3
K6	IO177RSB3
K7	GND
K8	GND
K9	GND
K10	GND
K11	GND
K12	IO88RSB1
K13	IO94RSB1
K14	IO95RSB1
K15	IO93RSB1
K16	GND
K17	GCC2/IO87RSB1
L1	GFA2/IO188RSB3
L2	GFC2/IO186RSB3
L3	IO182RSB3
L4	GND
L5	IO173RSB3
L6	GEC1/IO170RSB3
L7	GND
L8	GND
L9	VCC
L10	GND
L11	GND
L12	GDC1/IO99RSB1
L13	GDB1/IO101RSB1
L14	VCCIB1
L15	IO98RSB1
L16	IO92RSB1
L17	IO91RSB1
M1	IO184RSB3
M2	VCCIB3
M3	IO176RSB3
M4	IO172RSB3
M5	GEB0/IO167RSB3
M6	GEB1/IO168RSB3
M7	IO159RSB2
M8	IO161RSB2
M9	IO135RSB2
M10	IO128RSB2
M11	IO121RSB2
M12	IO113RSB2
M13	GDA1/IO103RSB1
M14	GDA0/IO104RSB1
M15	IO97RSB1
M16	IO96RSB1
M17	VCCIB1
N1	IO180RSB3
N2	IO178RSB3
N3	GEC0/IO169RSB3
N4	GEA0/IO165RSB3
N5	GND
N6	IO156RSB2
N7	IO148RSB2
N8	IO144RSB2
N9	IO137RSB2
N10	VCCIB2
N11	IO119RSB2
N12	IO111RSB2
N13	GDB2/IO106RSB2
N14	IO109RSB2
N15	GND
N16	GDB0/IO102RSB1
N17	GDC0/IO100RSB1
P1	IO174RSB3
P2	IO171RSB3
P3	GND
P4	IO160RSB2
P5	IO157RSB2
P6	IO154RSB2
P7	IO152RSB2

CS289	
Pin Number	**AGLP125 Function**
P8	GND
P9	IO132RSB2
P10	IO125RSB2
P11	IO126RSB2
P12	IO112RSB2
P13	VCCIB2
P14	IO108RSB2
P15	GDA2/IO105RSB2
P16	GDC2/IO107RSB2
P17	VJTAG
R1	GND
R2	GEA2/IO164RSB2
R3	IO158RSB2
R4	IO155RSB2
R5	IO150RSB2
R6	VCCIB2
R7	IO145RSB2
R8	IO141RSB2
R9	IO134RSB2
R10	IO130RSB2
R11	GND
R12	IO118RSB2
R13	IO116RSB2
R14	IO114RSB2
R15	IO110RSB2
R16	TMS
R17	TRST
T1	GEA1/IO166RSB3
T2	GEC2/IO162RSB2
T3	IO153RSB2
T4	GND
T5	IO147RSB2
T6	IO143RSB2
T7	IO140RSB2
T8	IO139RSB2
T9	VCCIB2
T10	IO131RSB2
T11	IO127RSB2

CS289	
Pin Number	**AGLP125 Function**
T12	IO124RSB2
T13	IO122RSB2
T14	GND
T15	IO115RSB2
T16	TDI
T17	TDO
U1	FF/GEB2/IO163RSB2
U2	GND
U3	IO151RSB2
U4	IO149RSB2
U5	IO146RSB2
U6	IO142RSB2
U7	GND
U8	IO138RSB2
U9	IO136RSB2
U10	IO133RSB2
U11	IO129RSB2
U12	GND
U13	IO123RSB2
U14	IO120RSB2
U15	IO117RSB2
U16	TCK
U17	VPUMP

Revision	Changes	Page
Revision 11 (continued)	The tables in the "Single-Ended I/O Characteristics" section were updated. Notes clarifying IIL and IIH were added. Tables for 3.3 V LVCMOS and 1.2 V LVCMOS wide range were added (SAR 79370, SAR 79353, and SAR 79366). Notes in the wide range tables state that the minimum drive strength for any LVCMOS 3.3 V (or LVCMOS 1.2 V) software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models (SAR 25700).	2-27
	The following sentence was deleted from the "2.5 V LVCMOS" section: It uses a 5 V–tolerant input buffer and push-pull output buffer (SAR 24916).	2-32
	The tables in the "Input Register" section, "Output Register" section, and "Output Enable Register" section were updated. The tables in the "VersaTile Characteristics" section were updated.	2-45 through 2-56
	The following tables were updated in the "Global Tree Timing Characteristics" section: Table 2-85 • AGLP060 Global Resource (1.5 V) Table 2-86 • AGLP125 Global Resource (1.5 V) Table 2-88 • AGLP060 Global Resource (1.2 V)	2-58
	Table 2-90 • IGLOO PLUS CCC/PLL Specification and Table 2-91 • IGLOO PLUS CCC/PLL Specification were revised (SAR 79388). VCO output jitter and maximum peak-to-peak jitter data were changed. Three notes were added to the table in connection with these changes.	2-61
	Figure 2-28 • Write Access after Write onto Same Address and Figure 2-29 • Write Access after Read onto Same Address were deleted.	N/A
	The tables in the "SRAM", "FIFO" and "Embedded FlashROM Characteristics" sections were updated.	2-68, 2-78

Revision	Changes	Page
Revision 3 (continued)	The table note for Table 2-9 • Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Flash*Freeze Mode* to remove the sentence stating that values do not include I/O static contribution.	2-7
	The table note for Table 2-10 • Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Sleep Mode* was updated to remove VJTAG and VCCI and the statement that values do not include I/O static contribution.	2-7
	The table note for Table 2-11 • Quiescent Supply Current (IDD) Characteristics, IGLOO PLUS Shutdown Mode was updated to remove the statement that values do not include I/O static contribution.	2-7
	Note 2 of Table 2-12 • Quiescent Supply Current (IDD), No IGLOO PLUS Flash*Freeze Mode 1 was updated to include VCCPLL. Table note 4 was deleted.	2-8
	Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings and Table 2-14 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings[1] were updated to remove static power. The table notes were updated to reflect that power was measured on VCC_I. Table note 2 was added to Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings.	2-9, 2-9
	Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices and Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices were updated to change the definition for P_{DC5} from bank static power to bank quiescent power. Table subtitles were added for Table 2-16 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices, Table 2-17 • Different Components Contributing to Dynamic Power Consumption in IGLOO PLUS Devices, and Table 2-18 • Different Components Contributing to the Static Power Consumption in IGLOO PLUS Devices.	2-10, 2-11
	The "Total Static Power Consumption—P_{STAT}" section was revised.	2-12
	Table 2-32 • Schmitt Trigger Input Hysteresis is new.	2-26
Packaging v1.3	The "CS281" package drawing is new.	4-13
	The "CS281" table for the AGLP125 device is new.	4-13
Revision 3 (continued)	The "CS289" package drawing was incorrect. The graphic was showing the CS281 mechanical drawing and not the CS289 mechanical drawing. This has now been corrected.	4-17
Revision 2 (Jun 2008) Packaging v1.2	The "CS289" table for the AGLP030 device is new.	4-17
Revision 1 (Jun 2008) Packaging v1.1	The "CS289" table for the AGLP060 device is new.	4-20
	The "CS289" table for the AGLP125 device is new.	4-23